Abstracts

A S-band push-pull 60-watt GaAs MESFET for MMDS applications

G. Sarkissian, R. Basset, Z. Shingu and F. Ono. "A S-band push-pull 60-watt GaAs MESFET for MMDS applications." 1997 MTT-S International Microwave Symposium Digest 3. (1997 Vol. III [MWSYM]): 1409-1412.

A new 2.5-2.7 GHz High-Power GaAs FET for the MMDS application is presented. It uses two pairs of pre-matched chips mounted on the same carrier and combined in push-pull configuration with a microstrip balun. This device exhibits 60 W of output power with 11.0 dB of gain. This is the highest power reported for such a device.

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